AMP1068
SOLID STATE HIGH POWER AMPLIFIER

FEATURES

Class AB hybrid GaAsFET Chip & Wire technology
Instantaneous ultra-wide Bandwidth
Designed for EMI/RFI, lab, and general communication applications
Suitable for all single channel modulation standards
Built-in protection circuits
High reliability and ruggedness

ELECTRICAL SPECIFICATIONS: 50Ω, 25°C

Parameter	Specification	Notes
Operating Frequency Range	6.0 - 18.0 GHz	
Power Output Psat	10 Watt Min	CW
Power Gain	40 dB Min	
Power Gain Flatness	4.0 dB p-p Max	
Input Return Loss	-10 dB Max	50 Ohm reference
Harmonics	-15 dBc Typ	At rated Pout
Noise Figure	10 dB Max	
Spurious	-60 dBc Max	Non-harmonics
Operating Voltage	12 VDC Nom	
Current Consumption	13 Amp Max. / <12 Amp Typ	At rated Pout
Input Power Protection	+3 dBm Max	<10 Sec without damage
Load VSWR Protection	5 : 1 Max	<1 minute at rated Pout

ENVIRONMENTAL CHARACTERISTICS

Parameter	Specification	Notes
Operating Case Temperature	-20 to +65 °C	
Storage Temperature	-40 to +85 °C	
Relative Humidity	5 to 95 %	Non-condensing

MECHANICAL SPECIFICATIONS

Parameter	Specification	Notes
Dimensions	100 x 100 x 27 mm	Excluding connectors
Weight	600 gr.	
RF Connectors In / Out	Hi Freq. SMA-female	
DC Power / Interface Connector	9-Pin D-Sub	
Cooling	External Heatsink	Forced air required

D-SUB CONNECTOR PIN ASSIGNMENT

Pin	Function	Description
1		N/A
2		N/A
3	Current Sensor	I_D@20mV/100mA Typ
4	Temp Sensor	V_T@10mV/°C + 500mV Typ
5	Shutdown	Enable = TTL “Hi” or open / Disable = TTL “Lo” or short
6, 7	VDD	12VDC
8, 9	GND	Ground

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OUTLINE DRAWING